MSKSEMI















ESD

TVS

TSS

MOV

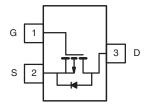
GDT

PLED

Broduct data sheet



SOT-23



Features

- -18V, -2.0A, RDS(ON) $=60m\Omega$ @VGS = -4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-18V	$60 \text{m}\Omega$	-2.0A

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-18	V
V _{GS}	Gate-Sou₁ce Voltage	± 12	V
1	Drain Current – Continuous (T _C =25°C)	-2.0	Α
I _D	Drain Current – Continuous (T _C =100°C)	-0.95	А
I _{DM}	Drain Current – Pulsed ¹	-8.0	А
D	Power Dissipation (T _C =25°C)	312	mW
P _D	Power Dissipation – Derate above 25℃	2.5	mW/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		400	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-18			V
BV _{DSS} T _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.01		V/°C
	Drain Source Lookege Current	V _{DS} =-18V , V _{GS} =0V , T _J =25			-1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V , V _{GS} =0V , T _J =125			-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} 12V , V _{DS} =0V			100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-2A		60	110	
TUDS(ON)		V _{GS} =-2.5V , I _D =-1A		110	135	mΩ
V _{GS(th)}	Gate Threshold Voltage	\/ =\/ = 250\	-0.3	-0.6	-1.0	V
V _{GS(th)}	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		3		mV/∘c
gfs	Forward Transconductance	V _{DS} =-10V , I _S =-1A		2.2		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2, 3}		 4.8	8	
Q _{gs}	Gate-Source Charge ^{2, 3}	V _{DS} =-10V , V _{GS} =-4.5V , I _D =-1A	 0.5	1	nC
Q_{gd}	Gate-Drain Charge ^{2, 3}		 1.9	4	
T _{d(on)}	Turn-On Delay Time ^{2, 3}		 3.5	7	
Tr	Rise Time ^{2,3}	V_{DD} =-10V , V_{GS} =-4.5V , R_{G} =25 Ω	 12.6	24	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}	I _D =-1A	 32.6	62	ns
T _f	Fall Time ^{2, 3}		 8.4	16	
C _{iss}	Input Capacitance		 350	510	
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz	 65	95	pF
C _{rss}	Reverse Transfer Capacitance		 50	75	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V . Force Current			-2.0	Α
I _{SM}	Pulsed Source Current	TVG-VD-UV, FOICE Current			-4.0	Α
V_{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

Note:

- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$.
- 3. Essentially independent of operating temperature.



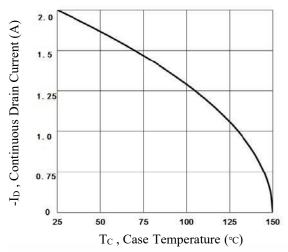


Fig.1 Continuous Drain Current vs. Tc

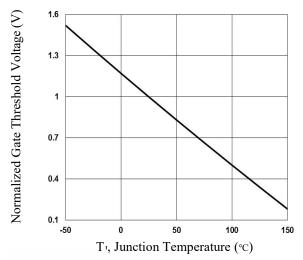


Fig.3 Normalized V_{th} vs. T_J

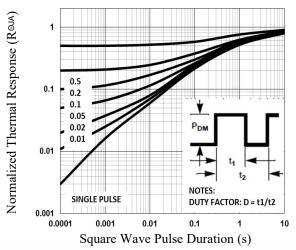


Fig.5 Normalized Transient Response

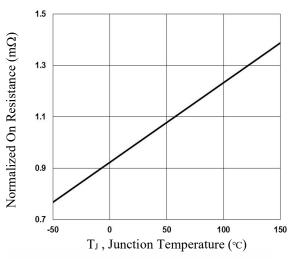


Fig.2 Normalized RDSON vs. T_J

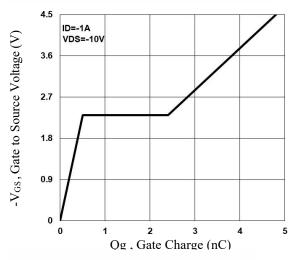


Fig.4 Gate Charge Waveform

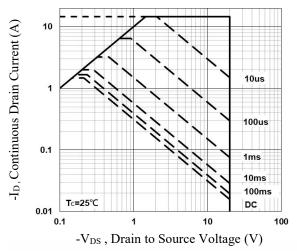
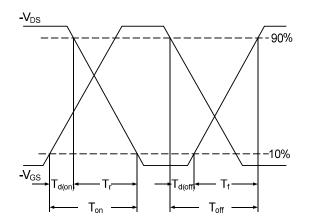


Fig.6 Maximum Safe Operation Area







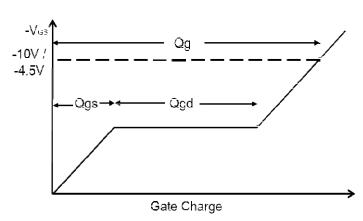
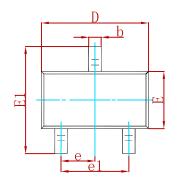


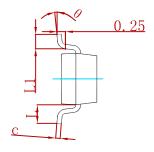
Fig.8 Gate Charge Waveform

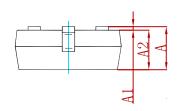




PACKAGE MECHANICAL DATA

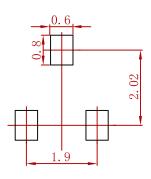






Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550) REF	0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
NTR2101PT1G-MS	SOT-23	3000



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